ALPHANUMERIC INDEX — CROSS-REFERENCE

The following table represents an index and cross-reference guide for all low-frequency power transistors which are either manufactured directly by Motorola or for which Motorola manufactures a suitable equivalent. Where the Motorola part number differs from the industry part number, the Motorola device is a "form, fit and function" replacement for the industry type number — however, subtle differences in characteristics and/or specifications may exist.

1

Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
1SI10A-100		MJ16018	3-782
2N1487		2N5877	3-120
2N1488		2N5878	3-120
2N1489		2N5877	3-120
2N1490		2N5878	3-120
2N1702		2N5877	3-120
2N3016		2N5337	3-97
2N3021		2N3789	3-56
2N3022		2N3789	3-56
2N3023		2N3789	3-56
2N3024		2N3791	3-56
2N3025		2N3791	3-56
2N3026		2N3791	3-56
2N3054	2N3054		3-2
2N3054A	2N3054A		3-2
2N3055	2N3055		3-6
2N3055A	2N3055A		3-9
2N3055H		2N3055A	3-9
2N3055JAN		2N5302JAN	3-93
2N3055SD		2N3055A	3-9
2N3055UB		2N3055A	3-9
2N3076		2N6249	3-164
2N3079		2N6308	3-181
2N3080		2N6543	3-215
2N3171		2N3789	3-56
2N3172		2N3789	3-56
2N3173		2N3790	3-56
2N3174		MJ15016	3-9
2N3183		2N3789	3-56
2N3184		2N3789	3-56
2N3185		2N3790	3-56
2N3186		MJ15016	3-9
2N3195		2N3789	3-56
2N3196		2N3790	3-56
2N3198		MJ15016	3-9
2N3202		2N3719	3-32
2N3203		2N3720	3-32
2N3204		2N6303	3-32
2N3232		2N5877	3-120
2N3233		2N5882	3-123
2N3234		2N5760	3-116
2N3235		2N3055	3-6
2N3236		2N5882	3-123
2N3237		2N5302	3-93
2N3238		2N5882	3-123
2N3239		2N5882	3-123
2N3240		2N5882	3-123
2N3419		2N5336	3-97
2N3420		2N5336	3-97
2N3421		2N5336	3-97

Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
2N3441	2N3441		3-13
2N3442	2N3442		3-15
2N3445	2N3447		3-18
2N3446	2N3448		3-18
2N3447	2N3447		3-18
2N3448	2N3448		3-18
2N3583	2N3583		3-20
2N3584	2N3584		3-20
2N3585	2N3585		3-20
2N3667		2N5881	3-123
2N3713		2N5881	3-123
2N3714	2N3714		3-26
2N3715	2N3715		3-26
2N3715JAN	2N3715JAN		3-26
2N3715JTX	2N3715JTX		3-26
2N3715JTXV	2N3715JTXV		3-26
2N3716	2N3716		3-26
2N3716JAN	2N3716JAN		3-26
2N3716JTX	2N3716JTX		3-26
2N3716JTXV	2N3716JTXV		3-26
2N3719	2N3719		3-32
2N3720	2N3720		3-32
2N3738	2N3738		3-37
2N3739	2N3739		3-37
2N3739JAN	2N3739JAN		3-37
2N3739JTX	2N3739JTX		3-37
2N3739JTXV	2N3739JTXV		3-37
2N3740	2N3740		3-41
2N3740A		2N3740	3-41
2N3740JAN	2N3740JAN		3-41
2N3740JTX	2N3740JTX		3-41
2N3740JTXV	2N3740JTXV		3-41
2N3741	2N3741		3-41
2N3741A	2N3741A		3-41
2N3741JAN	2N3741JAN		3-41
2N3741JTX	2N3741JTX		3-41
2N3741JTXV	2N3741JTXV		3-41
2N3766	2N3766		3-44
2N3766JAN	2N3766JAN		3-44
2N3766JTX	2N3766JTX		3-44
2N3766JTXV	2N3766JTXV		3-44
2N3767	2N3767		3-44
2N3767JAN	2N3767JAN		3-44
2N3767JTX	2N3767JTX		3-44
2N3767JTXV	2N3767JTXV		3-44
2N3771	2N3771		3-48
2N3772	2N3772		3-48
2N3773	2N3773		3-52
2N3788		2N6543	3-215
2N3789	2N3789		3-56

TABLE 1 — METAL TO-204, TO-204AE (continued)

I_CCont Amps Max	$V_{CEO(sus)}$ Volts Min	Device Type NPN	Device Type PNP	h_{FE} Min/Max	@ I_C Amp	Resistive Switching t_s µs Max	Resistive Switching t_f µs Max	Resistive Switching @ I_C Amp	f_T MHz Min	P_D (Case) Watts @ 25°C
10	250	MJ15011	MJ15012	20/100	2					200
	300	MJ3041##		250 min	2.5					175
	325	MJ413		20/80	0.5				2.5	125
		MJ423		30/90	1				2.5	125
		MJ431		15/35	2.5				2.5	125
	350	BU323##		150 min	6	7.5 typ	5.2 typ	6		175
		MJ3042##		250 min	2.5					175
		MJ13014		8/20	5	2	0.5	5		150
		MJ10002##		3/300	5	2.5	1	5	10#	150
		MJ10006##		30/300	5	1.5	0.5	5	10#	150
	400	BU323A##		150 min	6	7.5 typ	5.2 typ	6		175
		MJ10007##		30/300	5	1.5	0.5	5	10#	150
		MJ10012##		100/2k	6	15	15	6		175
		MJ13015		8/20	5	2	0.5	5		150
	600	MJ10014##		10/250	10	2.5	0.8	10		175
	700	MJ8504		7.5 min	1.5	4	2	5		175
	800	MJ8505		7.5 min	1.5	4	2	5		175
		MJ16018		4 min	5	4.5 typ	0.2 typ	5		150
	950*	MJ12010		4.2 min	5		1	5		100
12	60	2N6057##	2N6050##	750/18k	6	1.6 typ	1.5 typ	6	4#	150
	80	2N6058##	2N6051##	750/18k	6	1.6 typ	1.5 typ	6	4#	150
	100	2N6059##	2N6052##	750/18k	6	1.6 typ	1.5 typ	6	4#	150
15	60	2N3055	MJ2955	20/70	4	0.7 typ	0.3 typ	4	2.5	115
		2N3055A	MJ2955A	20/70	4				0.8	115
		2N6576##		2k/20k	4	2	7	10	10–200#	120
		2N5881	2N5879	20/100	6	1	0.8	6	4	160
	80	2N5882	2N5880	20/100	6	1	0.8	6	4	160
	90	2N6577##		2k/20k	4	2	7	10	10-200#	120
	120	MJ15015	MJ15016	20/70	4				1	180
		2N6578##		2k/20k	4	2	7	10	10-200#	120
	140	MJ15001	MJ15002	25/150	4				2	200
	150	MJ11018##	MJ11017##	100 min	15				3#	175
	200	BUX41		8 min	8	1.5	0.4	8	8	120
		2N6249		10/50	10	3.5	1	10	2.5	175
		MJ11020##	MJ11019##	100 min	15				3#	175
	250	MJ11022##	MJ11021##	100 min	15				3#	175
	275	2N6250		8/50	10	3.5	1	10	2.5	175
	300	2N6546		6/30	10	4	0.7	10	6 to 24	175
	325	BUX13		8 min	8	2.5	0.8	8	8	150
	400	BUX48		8 min	10	2	0.4	10		175
		2N6547		6/30	10	4	0.7	10	6 to 24	175
		MJ13090		8 min	10	2.5	0.5	10		175
		MJ16110		6/20	15	0.8 typ	0.1 typ	10		175
	450	BUX48A		8 min	8	2	0.4	10		175
		MJ16010		5 min	15	1.2 typ	0.2 typ	10		175

* $V_{(BR)CEX}$, # $|h_{fe}|$ @ 1 MHz, ## Darlington

(continued)

☐ JAN, JTX, JTXV Available

NPN 2N3055 PNP MJ2955

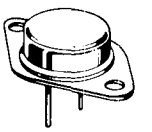
COMPLEMENTARY SILICON POWER TRANSISTORS

. . . designed for general-purpose switching and amplifier applications.

- DC Current Gain – h_{FE} = 20-70 @ I_C = 4 Adc
- Collector-Emitter Saturation Voltage – $V_{CE(sat)}$ = 1.1 Vdc (Max) @ I_C = 4 Adc
- Excellent Safe Operating Area

15 AMPERE POWER TRANSISTORS COMPLEMENTARY SILICON

60 VOLTS
115 WATTS



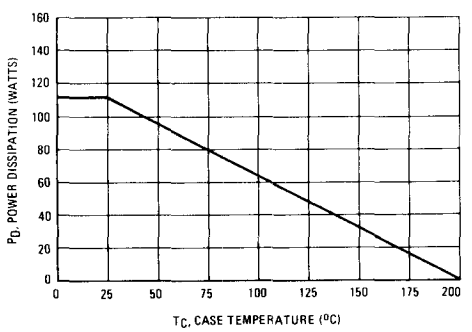
MAXIMUM RATINGS

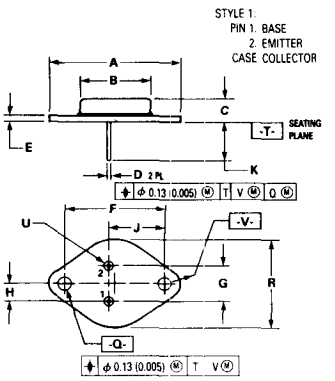
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	60	Vdc
Collector-Emitter Voltage	V_{CER}	70	Vdc
Collector-Base Voltage	V_{CB}	100	Vdc
Emitter-Base Voltage	V_{EB}	7	Vdc
Collector Current – Continuous	I_C	15	Adc
Base Current	I_B	7	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	115 0.657	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.52	°C/W

FIGURE 1 – POWER DERATING





DIM	MILLIMETERS MIN	MILLIMETERS MAX	INCHES MIN	INCHES MAX
A	—	39.37	—	1.550
B	—	21.08	—	0.830
C	6.35	8.25	0.250	0.325
D	0.97	1.09	0.038	0.043
E	1.40	1.77	0.055	0.070
F	30.15 BSC		1.187 BSC	
G	10.92 BSC		0.430 BSC	
H	5.46 BSC		0.215 BSC	
J	16.89 BSC		0.665 BSC	
K	11.18	12.19	0.440	0.480
Q	3.84	4.19	0.151	0.165
R	—	26.67	—	1.050
U	4.83	5.33	0.190	0.210
V	3.84	4.19	0.151	0.165

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

CASE 1-06
TO-204AA
(TO-3)

3

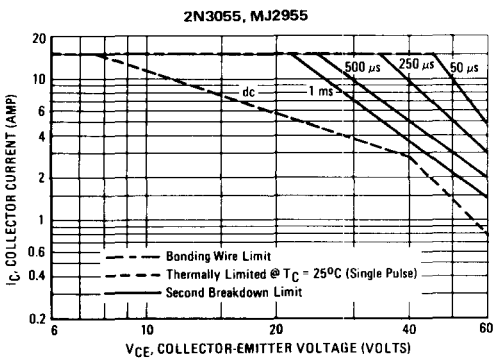
ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
***OFF CHARACTERISTICS**				
Collector-Emitter Sustaining Voltage (1) (I_C = 200 mAdc, I_B = 0)	$V_{CEO(sus)}$	60	–	Vdc
Collector-Emitter Sustaining Voltage (1) (I_C = 200 mAdc, R_{BE} = 100 Ohms)	$V_{CER(sus)}$	70	–	Vdc
Collector Cutoff Current (V_{CE} = 30 Vdc, I_B = 0)	I_{CEO}	–	0.7	mAdc
Collector Cutoff Current (V_{CE} = 100 Vdc, $V_{BE(off)}$ = 1.5 Vdc) (V_{CE} = 100 Vdc, $V_{BE(off)}$ = 1.5 Vdc, T_C = 150°C)	I_{CEX}	 – –	 1.0 5.0	mAdc
Emitter Cutoff Current (V_{BE} = 7.0 Vdc, I_C = 0)	I_{EBO}	–	5.0	mAdc
***ON CHARACTERISTICS (1)**				
DC Current Gain (I_C = 4.0 Adc, V_{CE} = 4.0 Vdc) (I_C = 10 Adc, V_{CE} = 4.0 Vdc)	h_{FE}	 20 5.0	 70 –	–
Collector-Emitter Saturation Voltage (I_C = 4.0 Adc, I_B = 400 mAdc) (I_C = 10 Adc, I_B = 3.3 Adc)	$V_{CE(sat)}$	 –	 1.1 3.0	Vdc
Base-Emitter On Voltage (I_C = 4.0 Adc, V_{CE} = 4.0 Vdc)	$V_{BE(on)}$	–	1.5	Vdc
SECOND BREAKDOWN				
Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 40 Vdc, t = 1.0 s; Nonrepetitive)	$I_{s/b}$	2.87	–	Adc
DYNAMIC CHARACTERISTICS				
Current Gain – Bandwidth Product (I_C = 0.5 Adc, V_{CE} = 10 Vdc, f = 1.0 MHz)	f_T	2.5	–	MHz
*Small-Signal Current Gain (I_C = 1.0 Adc, V_{CE} = 4.0 Vdc, f = 1.0 kHz)	h_{fe}	15	120	–
*Small-Signal Current Gain Cutoff Frequency (V_{CE} = 4.0 Vdc, I_C = 1.0 Adc, f = 1.0 kHz)	f_{hfe}	10	–	kHz

* Indicates Within JEDEC Registration. (2N3055)

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

FIGURE 2 – ACTIVE REGION SAFE OPERATING AREA



There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on T_C = 25°C; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated for temperature according to Figure 1.

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